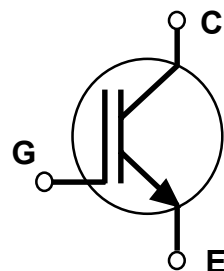
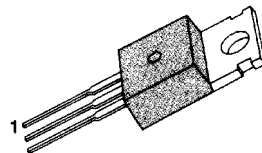


FEATURES

- * High Speed Switching
- * Low Saturation Voltage
: $V_{CE(sat)} = 2.0 \text{ V}$ (@ $I_C = 20\text{A}$)
- * High Input Impedance

APPLICATIONS

- * AC & DC Motor controls
- * General Purpose Inverters
- * Robotics , Servo Controls
- * Power Supply
- * Lamp Ballast

TO-220**ABSOLUTE MAXIMUM RATINGS**

Symbol	Characteristics	Rating	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_c = 25^\circ\text{C}$	40	A
	Collector Current @ $T_c = 100^\circ\text{C}$	20	A
$I_{CM(1)}$	Pulsed Collector Current	160	A
P_C	Maximum Power Dissipation @ $T_c = 25^\circ\text{C}$	160	W
	Maximum Power Dissipation @ $T_c = 100^\circ\text{C}$	64	W
T_j	Operating Junction Temperature	$-55 \sim 150$	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	$-55 \sim 150$	$^\circ\text{C}$
T_L	Maximum Lead Temp. For Soldering	300	$^\circ\text{C}$
	Purposes, $\frac{1}{8}$ " from case for 5 seconds		

Notes:(1) Repetitive rating : Pulse width limited by max. junction temperature

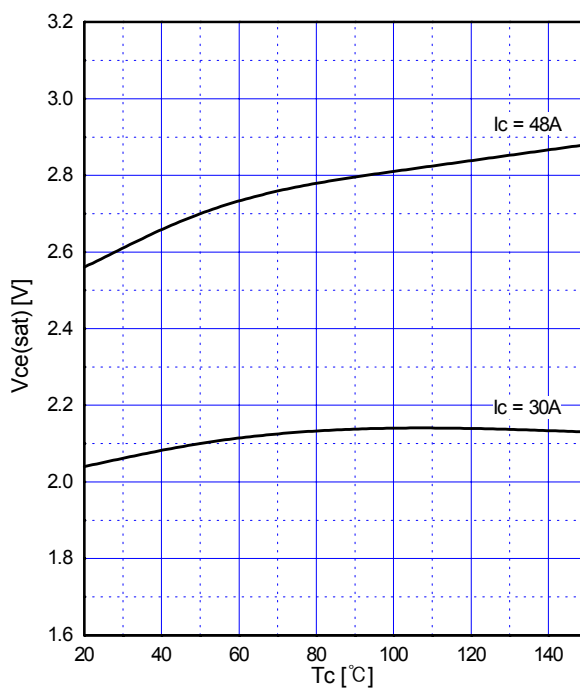
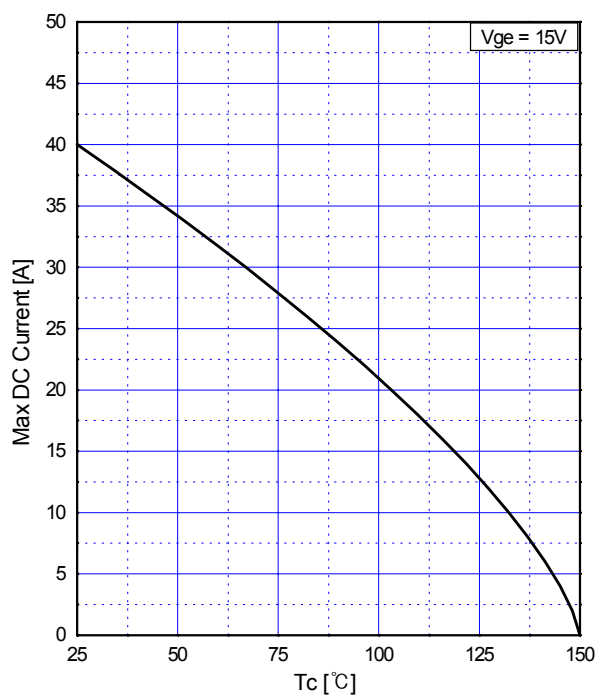
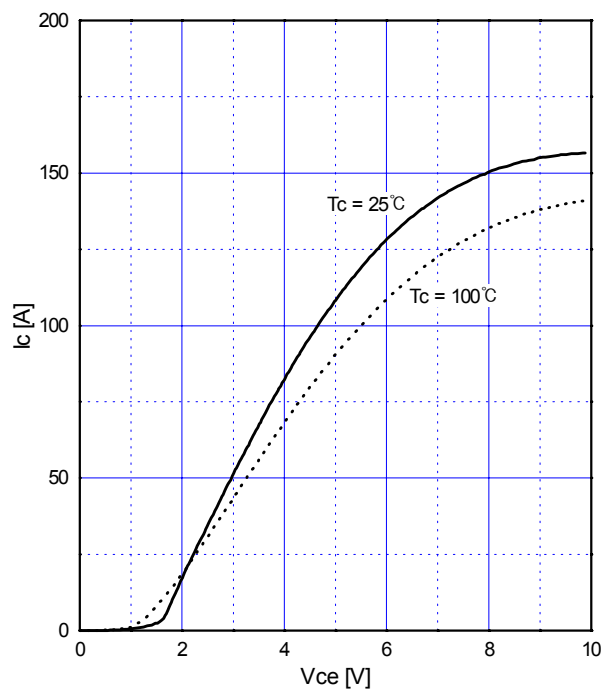
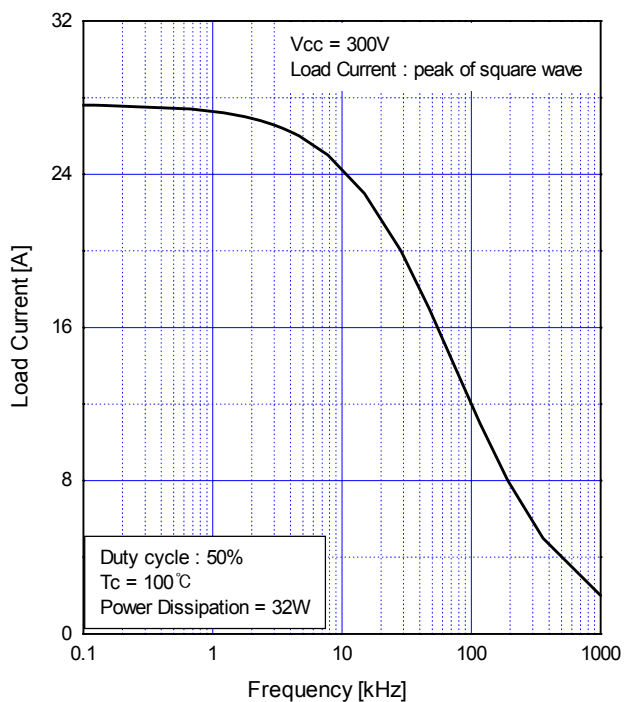
ELECTRICAL CHARACTERISTICS)(T_c=25°C, Unless Otherwise Specified)

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Units
BV _{CES}	C - E Breakdown Voltage	V _{GE} = 0V , I _C = 250μA	600	-	-	V
$\Delta V_{CES} / \Delta T_J$	Temperature Coeff. of Breakdown Voltage	V _{GE} = 0V , I _C = 1mA	-	0.6	-	V/°C
V _{GE(th)}	G - E threshold voltage	I _C = 20mA , V _{CE} = V _{GE}	4.5	5.5	7.5	V
I _{CES}	Collector cutoff Current	V _{CE} = V _{CES} , V _{GE} = 0V	-	-	250	uA
I _{GES}	G - E leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	-	-	100	nA
V _{CE(sat)}	Collector to Emitter saturation voltage	I _C =20A, V _{GE} = 15V	-	2.0	2.6	V
		I _C =40A, V _{GE} = 15V	-	2.6	-	V
Cies	Input capacitance	V _{GE} = 0V , f = 1MHz V _{CE} = 30V	-	1430	-	pF
Coes	Output capacitance		-	120	-	pF
Cres	Reverse transfer capacitance		-	50	-	pF
td(on)	Turn on delay time	V _{CC} = 300V , I _C = 20A V _{GE} = 15V R _G = 10 Ω Inductive Load	-	12	-	ns
tr	Turn on rise time		-	20	-	ns
td(off)	Turn off delay time		-	68	100	ns
tf	Turn off fall time		-	50	100	ns
Eon	Turn on Switching Loss		-	0.08	-	mJ
Eoff	Turn off Switching Loss		-	0.19	-	mJ
Ets	Total Switching Loss		-	0.27	0.47	mJ
Qg	Total Gate Charge	V _{CC} = 300V	-	92	138	nC
Qge	Gate-Emitter Charge	V _{GE} = 15V	-	21	31	nC
Qgc	Gate-Collector Charge	I _C = 20A	-	28	42	nC
Le	Internal Emitter Inductance	Measured 5mm from PKG	-	7.5	-	nH

SGP40N60UF**N-CHANNEL IGBT**

THERMAL RESISTANCE

Symbol	Characteristics	Min	Typ	Max	Units
$R_{\theta JC}$	Junction-to-Case	-	-	0.77	°C/W
$R_{\theta JA}$	Junction-to-Case	-	-	80	°C/W
$R_{\theta CS}$	Case-to-Sink	-	0.5	-	°C/W



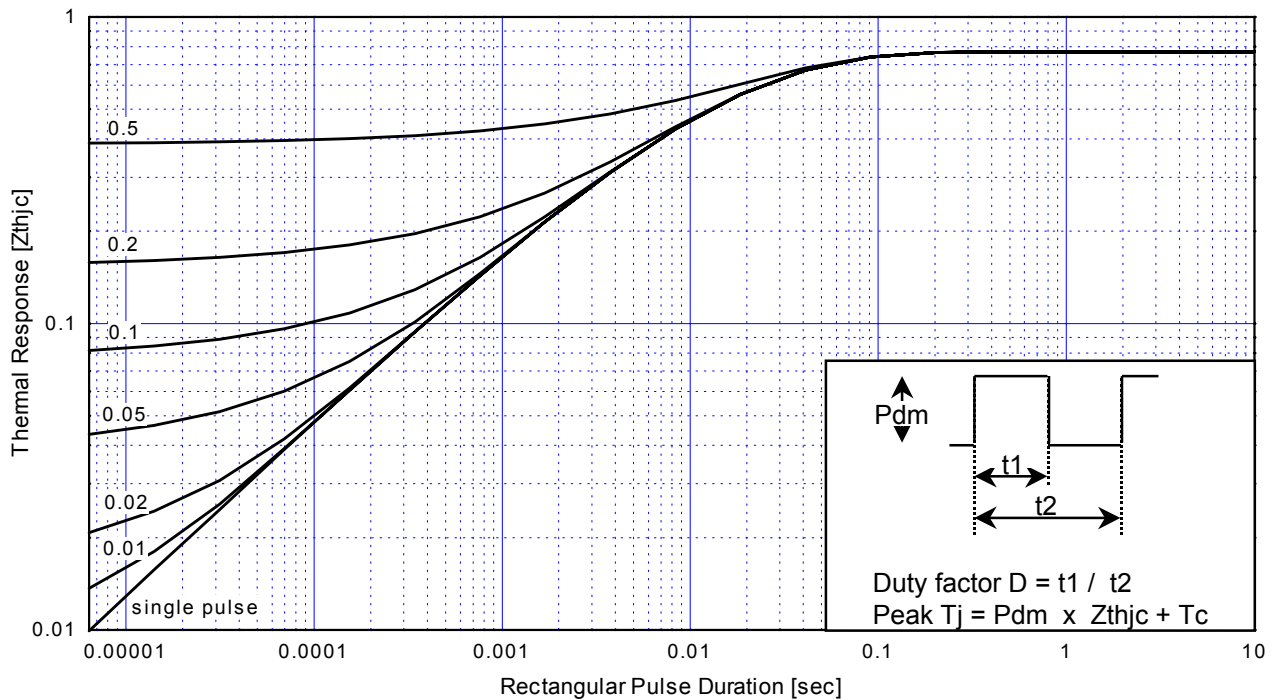
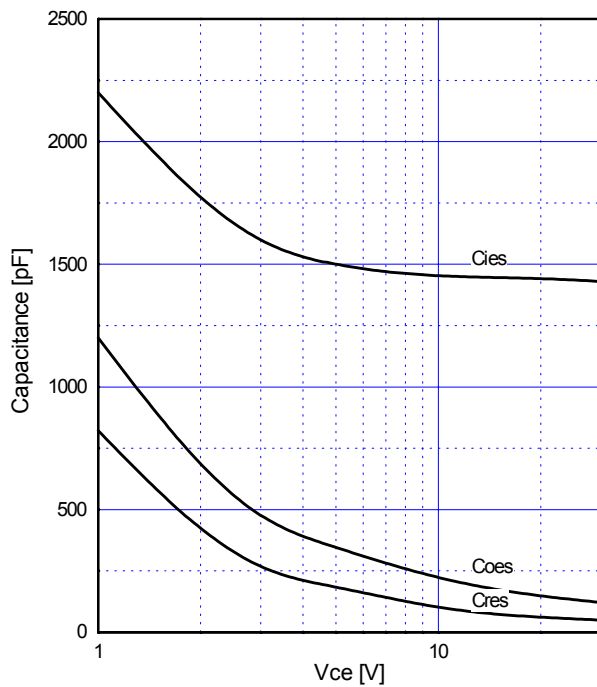
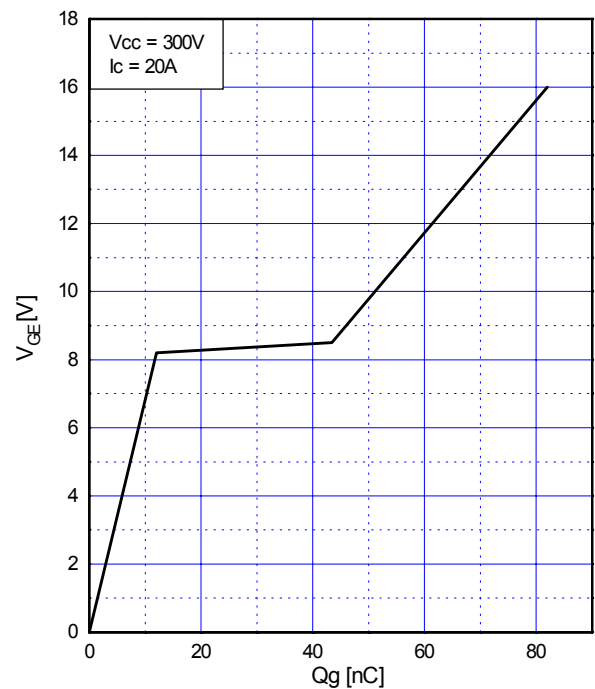


Fig.5 Maximum Effective Transient Thermal Impedance, Junction to Case

Fig.6 Typical Capacitance vs.
Collector to Emitter VoltageFig.7 Typical Gate Charge vs.
Gate to Emitter Voltage

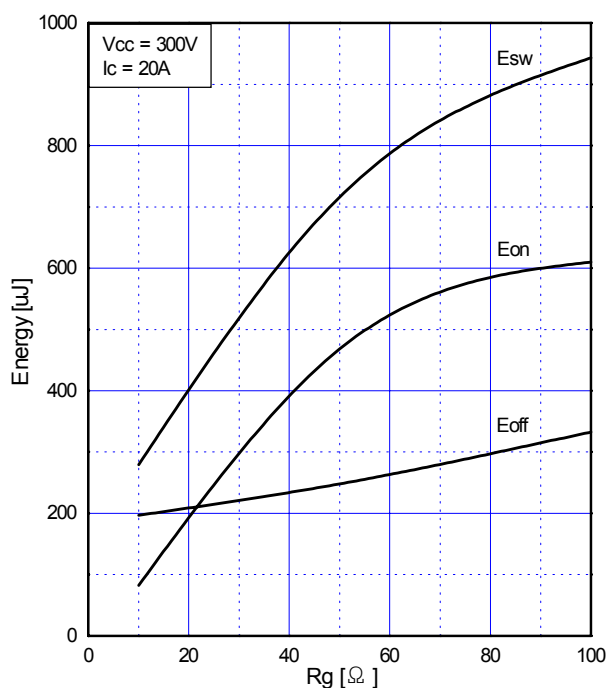


Fig.8 Typical Switching Loss vs. Gate Resistance

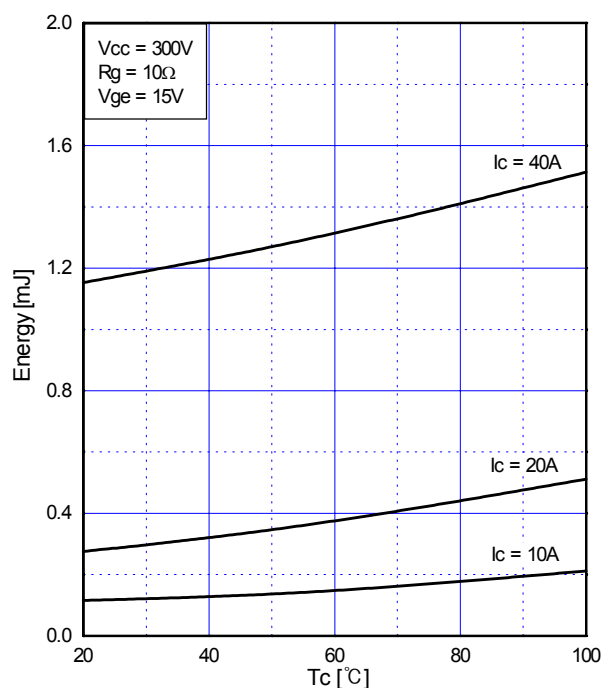


Fig.9 Typical Switching Loss vs. Case Temperature

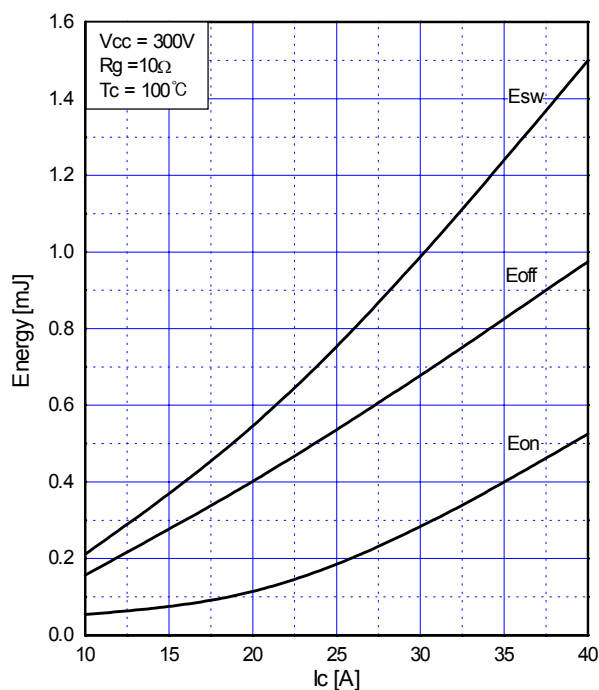


Fig.10 Typical Switching loss vs. Collector to Emitter Current

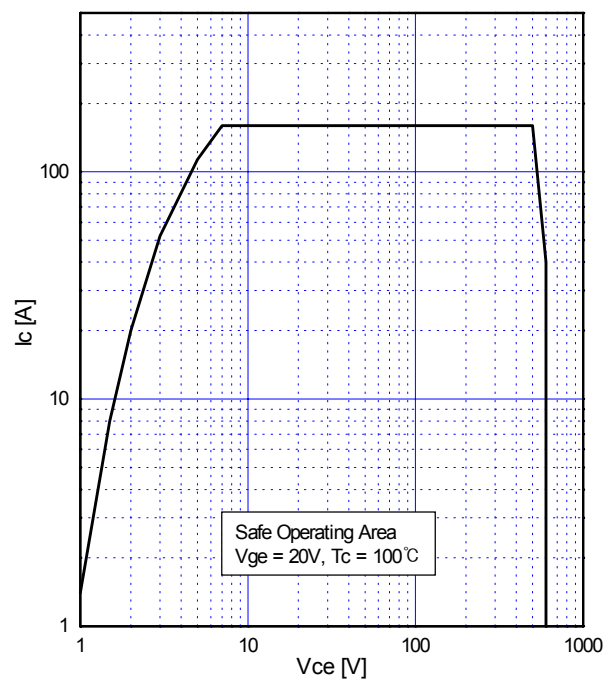


Fig.11 Turn-off SOA